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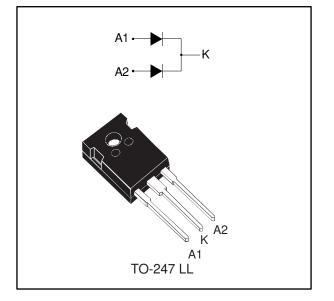




STPSC20H12C

1200 V power Schottky silicon carbide diode

Datasheet - production data



Features

- No or negligible reverse recovery
- Switching behavior independent of temperature
- Robust high voltage periphery
- Operating T_j from -40 °C to 175 °C
- ECOPACK[®]2 compliant

Description

The SiC diode, available in TO-247 LL, is an ultrahigh performance power Schottky rectifier. It is manufactured using a silicon carbide substrate. The wide band-gap material allows the design of a low VF Schottky diode structure with a 1200 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

Especially suited for use in PFC and secondary side applications, this ST SiC diode will boost the performance in hard switching conditions. This rectifier will enhance the performance of the targeted application. Its high forward surge capability ensures a good robustness during transient phases.

Table 1: Device summary

Symbol	Value
I _{F(AV)}	2 x 10 A
V _{RRM}	1200 V
T _j (max.)	175 °C
V _F (typ.)	1.35 V

February 2017

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This is information on a product in full production.

1 Characteristics

Table 2: Absolute ratings (limiting values per diode at 25 °C, unless otherwise specified)

Symbol		Value	Unit			
VRRM	Repetitive peak reverse	voltage (T _j = -40 °C to +175	°C)	1200	V	
I _{F(RMS)}	Forward rms current			25	А	
		$T_C = 150 \ ^\circ C$, DC current		10/20		
I _{F(AV)}	I _{F(AV)} Average forward	T _C = 135 °C, DC current	Per diode/per device	14/28	А	
	ourion	$T_C = 25 \ ^{\circ}C$, DC current		25/50		
IFRM	Repetitive peak forward current	$T_{C} = 150 \ ^{\circ}C, \ T_{j} = 175 \ ^{\circ}C,$	42	А		
			T _C = 25 °C	71		
I _{FSM}	I _{FSM} Surge non repetitive forward current	t _p = 10 ms sinusoidal	T _C = 150 °C	60	А	
		t _p = 10 μs square	Tc = 25 °C	420		
T _{stg}	Storage temperature range			-65 to +175	°C	
Tj	Operating junction temperature range			-40 to +175	°C	

Table 3: Thermal resistance parameters

Symbol	Parameter		Typ. value	Max. value	Unit
		Per diode	0.70	0.95	°C/W
R _{th(j-c)} Junction to case	Per device	0.35	0.48	°C/W	

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
IR ⁽¹⁾ Reverse leakage current	T _j = 25 °C		-	5	60		
	Reverse leakage current	T _j = 150 °C	$V_R = V_{RRM}$	-	30	400	μA
$\mathcal{M}_{-}(2)$	V _F ⁽²⁾ Forward voltage drop	T _j = 25 °C	I- 10 A	-	1.35	1.50	V
VF ⁽²⁾		T _j = 150 °C	I _F = 10 A	-	1.75	2.25	V

Notes:

$$\label{eq:powerset} \begin{split} & \mbox{$^{(1)}$Pulse test: t_p = 10 ms, δ < 2%$} \\ & \mbox{$^{(2)}$Pulse test: t_p = 500 μs, δ < 2%$} \end{split}$$

To evaluate the conduction losses, use the following equation:

 $P = 1.03 \; x \; I_{F(AV)} + 0.122 \; x \; I_{F^2(RMS)}$



Characteristics

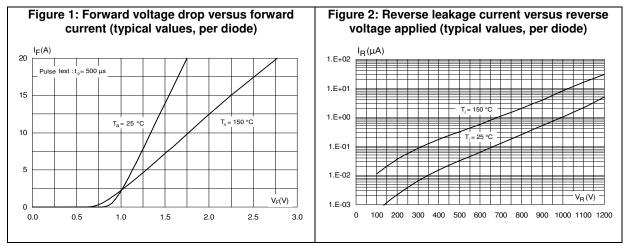
112C	Cha	racteri	stics				
	Table 5: Dynamic electrical characteristics (per diode)						
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit	
Qcj ⁽¹⁾	Total capacitive charge	V _R = 800 V	-	57	-	nC	
C		$V_R = 0 V$, $T_c = 25 \ ^\circ C$, $F = 1 \ MHz$	-	725	-	۶Ľ	
Cj	Total capacitance	$V_{\text{R}} = 800 \text{ V}, \text{T}_{\text{c}} = 25 ^{\circ}\text{C}, \text{F} = 1 \text{MHz}$	-	47	-	pF	

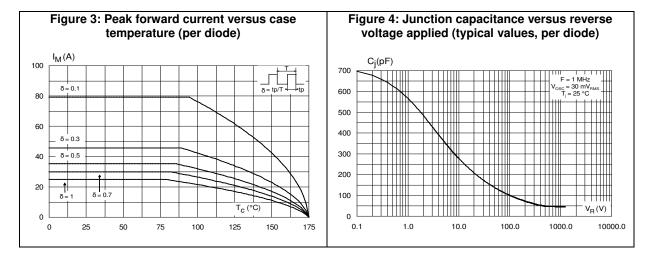
Notes:

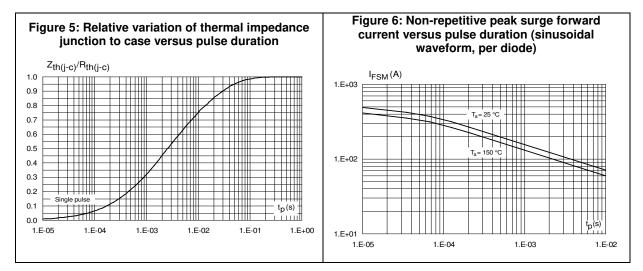
⁽¹⁾Most accurate value for the capacitive charge: $Q_{cj}(V_R) = \int_0^{V_R} C_j(V) dV$



1.1 Characteristics (curves)





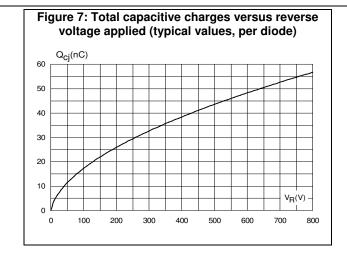


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Characteristics





2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK[®] is an ST trademark.

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.9 to 1.2 N·m



2.1

TO-247 long leads package information

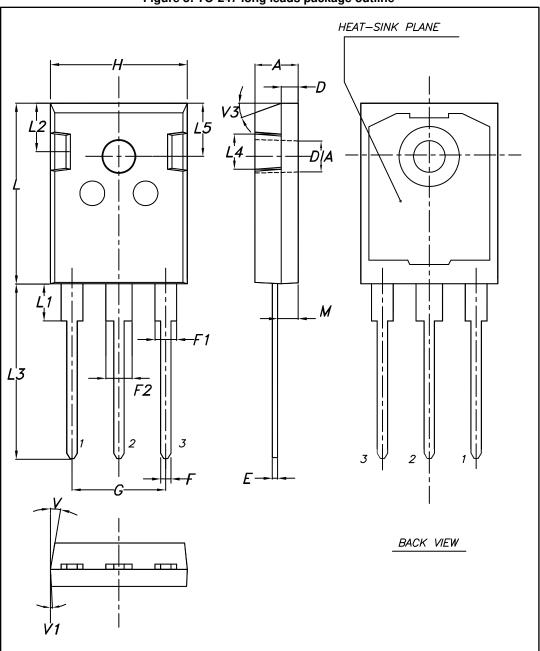


Figure 8: TO-247 long leads package outline



Package information

STPSC20H12C

Table 6: TO-247 long leads package mechanical data						
		mm.	<u> </u>		Inches	
Dim.	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	4.90		5.15	0.192		0.202
D	1.85		2.10	0.072		0.082
E	0.55		0.67	0.021		0.026
F	1.07		1.32	0.042		0.051
F1	1.90		2.38	0.074		0.093
F2	2.87		3.38	0.110		0.133
G		10.90 BSC			0.429 BSC	
Н	15.77		16.02	0.620		0.630
L	20.82		21.07	0.810		0.820
L1	4.16		4.47	0.163		0.175
L2	5.49		5.74	0.216		0.225
L3	20.05		20.30	0.789		0.799
L4	3.68		3.93	0.144		0.154
L5	6.04		6.29	0.237		0.247
М	2.25		2.55	0.088		0.100
V		10°			10°	
V1		3°			3°	
V3		20°			20°	
DIA	3.55		3.66	0.139		0.143

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3 Ordering information

Table 7: Ordering information						
Order code	Marking	Package	Weight	Base qty.	Delivery mode	
STPSC20H12CWL	STPSC20H12CWL	TO-247 LL	6.09 g	30	Tube	

4 Revision history

Table 8: Document revision history

Date	Revision	Changes
28-Feb-2017	1	Initial release.



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